



UNIVERSITI PUTRA MALAYSIA

**DIELECTRIC AND MAGNETIC CHARACTERIZATION OF
(La_{0.5-x}Pr_xBa_{0.5})(Mn_{0.5}Ti_{0.5})O₃ PEROVSKITE AS A
MULTIFERROIC MATERIAL SYNTHESIZED
VIA SOLID STATE TECHNIQUE**

**NOR HAYATI BT. ALIAS
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By

NOR HAYATI BT. ALIAS

Thesis Submitted to the School of Graduate Studies, Universiti Putra Malaysia, in
Fulfilment of the Requirements for the Degree of Master of Science

October 2009



DEDICATION

To god, my children and Dear husband

For the remembrance of my beloved late mother and father,

Friends, Universiti Putra Malaysia and Agency Nuclear Malaysia



Abstract of thesis presented to the Senate of Universiti Putra Malaysia in fulfilment of the requirement for the degree of Master of Science

**DIELECTRIC AND MAGNETIC CHARACTERIZATION OF
(La_{0.5-x}Pr_xBa_{0.5})(Mn_{0.5}Ti_{0.5})O₃ PEROVSKITE AS A MULTIFERROIC
MATERIAL SYNTHESIZED VIA SOLID STATE TECHNIQUE**

By

NOR HAYATI BT. ALIAS

October 2009

Chairman: Abdul Halim Shaari, PhD.

Faculty: Science

A new manganate perovskite (La_{0.5-x}Pr_xBa_{0.5})(Mn_{0.5}Ti_{0.5})O₃ has been prepared by ceramic solid-state technique at sintering temperature 1300 °C for 24 hours. The x concentration of Praseodymium (Pr) in molar proportion in A site has been varied as x = 0, 0.01, 0.02, 0.03, 0.04, 0.05, 0.06, 0.07, 0.08, 0.09, 0.1, 0.2, 0.3 and 0.4. The dielectric properties of the synthesized materials have been studied at frequency ranging from 5 Hz to 1 MHz from room temperature up to 200 °C. Furthermore, analyses have been carried out to determine the structural, magnetic and dielectric electrical properties of the synthesized material as a candidate of multiferroic material.

Pr (Praseodymium) addition would promote liquid phase sintering in the synthesized samples. This enhanced the agglomeration and porosity formation in the bulk volume. The defects and conducting liquid present would generate traps that



produce negative permittivity response at interfacial/space charge frequency region due to delay in transient current or situation in which inertial conducting current of the trap presents, exceeding the charging-discharging current component. The XRD (X-Ray Diffractometry) results indicate all samples possess a single phase monoclinic structure with space group P112. Multiferroic magnetodielectric coupling in material with ferromagnetic and high dielectric constant (> 30) is able to achieve in sample with x molar concentration = 0.07 at room temperature. The dielectric value obtained is 176 with loss $\tan \delta$ value 0.62. SEM/EDX analysis of the sample shows fine grain microstructure and high manganese (Mn) content (> 0.6 wt %) which favours the double exchange mechanism.

Comparing to unsubstituted Pr sample, $x=0$; sample with x molar concentration 0.2 and 0.4 shows enhanced dielectric values with additional loss. The range of dielectric value obtained for unsubstituted sample $x=0$ is 3117 to 12396 while for $x=0.2$ and $x=0.4$ the value range obtained is 1611 to 16316 and 967 to 13185 respectively. The increment is associated with both polarization and conduction mechanism process. Where, the dielectric constant and loss is contribution from the effect of space charge polarization and/or ion conducting motion. Respectively, generally higher values of dielectric constant is obtained in unsubstituted sample $x = 0$ and high x substituted concentration 0.1, 0.2, 0.3 and 0.4 as a result of dual relaxational polarization mechanisms existed in the frequency range studied. Dc conduction is found to be dominated the sample at high temperature regime and for low substituted sample with x molar concentration 0.01, 0.02, 0.03, 0.04, 0.05, 0.06, 0.07, 0.08 and 0.09. This is to suggest of enhanced mobility of localized charge carriers in liquid phase region. Whereas in sample Pr(X)0.07, dominated dc



conduction effect is due to fast ion hopping conduction in its fine grain microstructure with high Mn content.



Abstrak tesis yang dikemukakan kepada Senat Universiti Putra Malaysia sebagai memenuhi keperluan Ijazah Master Sains

**PENCIRIAN DIELEKTRIK DAN MAGNET $(La_{0.5-x}Pr_xBa_{0.5})(Mn_{0.5}Ti_{0.5})O_3$
PEROVSKITE SEBAGAI BAHAN MULTIFERROIC MELALUI TEKNIK
KEADAAN PEPEJAL**

Oleh

NOR HAYATI BT. ALIAS

Oktober 2009

Pengerusi: Abdul Halim Shaari, PhD.

Fakulti: Sains

Satu bahan baru seramik perovskite dari kumpulan manganit $(La_{0.5-x}Pr_xBa_{0.5})(Mn_{0.5}Ti_{0.5})O_3$ telah disediakan melalui teknik tindak balas keadaan pepejal pada suhu pensinteran $1300^\circ C$ selama 24 jam. Kepekatan x molar Praseodymium (Pr) pada kedudukan A pada perovskite telah ditetapkan sebagai $x = 0, 0.01, 0.02, 0.03, 0.04, 0.05, 0.06, 0.07, 0.08, 0.09, 0.1, 0.2, 0.3$ and 0.4 . Kajian dielektrik telah dikendalikan pada julat frekuensi 5 Hz sehingga 1 MHz dalam keadaan suhu bilik sehingga suhu mencapai $200^\circ C$. Analisa juga dilakukan untuk mengkaji sifat struktur, magnet dan dielektrik bahan yang telah disintesis serta melihat kesan pengkupelan multiferroik pada bahan yang dikaji.

Telah didapati bahawa kesan penggantian Pr (Praseodymium) ke atas bahan telah meningkatkan kesan pembentukan fasa solidus cecair pada mikrostruktur bahan.



Kesan agglomerasi dan pembentukan liang pada bahan juga adalah agak ketara. Ini memberi kesan kecacatan dalam bahan. Kecacatan serta kandungan fasa solidus cecair dalam mikrostruktur bahan telah mewujudkan kawasan negatif permittiviti spektra pada julat frekuensi interfisial. Ini adalah mungkin disebabkan oleh kesan kelambatan pada pergerakan arus peralihan elektrik atau disebabkan oleh kesan penghasilan arus inertia daripada perangkap kecacatan yang lebih besar. Analisis XRD (X-Ray Difraktometri) telah menunjukkan bahan yang disintesis mempunyai fasa tunggal hablur monoklinik P112. Adalah didapati juga bahawa kesan pengkupelan sifat dielektrik dan magnet berjaya diperolehi pada x dengan kepekatan molar 0.07. Sifatnya adalah feromagnetik dengan nilai pemalar dielektrik bahan 176 dan $\tan \delta$ 0.76 pada suhu bilik. Bahan ini juga didapati mempunyai mikrostruktur dengan saiz butiran yang kecil serta kandungan Mangan (Mn) yang agak tinggi (> 0.6 wt %) lantas menambahkan kesan mekanisma pertukaran ganda dua (DE) pada bahan.

Jika dibandingkan dengan bahan tanpa penggantian Pr iaitu $x=0$; sampel $x=0.2$ dan $x=0.4$ menunjukkan peningkatan nilai pemalar dielektrik juga nilai $\tan \delta$ nya. Julat nilai dielektrik yang diperolehi untuk sampel $x=0$ adalah 3117 to 12396. Sementara julat nilai yang diperolehi dari sampel dengan x molar kepekatan $x=0.2$ dan $x=0.4$ ialah 1611 - 16316 dan 967 - 13185. Keadaan ini adalah disebabkan oleh kedua-dua jenis mekanisma yang hadir pada bahan iaitu kesan relaksasi polarisasi serta kekonduksian. Dimana nilai pemalar dielektrik dan $\tan \delta$ yang diperolehi adalah gabungan daripada kesan polarisasi interfisial dan/atau konduksi pergerakan ion. Nilai pemalar dielektrik dengan x molar = 0, 0.1, 0.2, 0.3 dan 0.4 juga didapati lebih tinggi berbanding sampel x molar rendah. Ini disebabkan oleh wujudnya kesan dwi-

relaksasi polarisasi bahan pada campuran kepekatan tersebut. Bahan x molar rendah $x = 0.01, 0.02, 0.03, 0.04, 0.05, 0.06, 0.07, 0.08$ dan 0.09 menunjukkan kesan kekonduksian dc yang ketara terutamanya pada suhu tinggi. Ini mungkin disebabkan oleh kesan peningkatan cas yang bergerak pada kawasan solidus cecair bahan. Bagaimanapun kesan kekonduksian dc pada sampel Pr(X)0.07 ialah disebabkan oleh penambahan kelincahan pelompatan kekonduksian ion bebas bagi mikrostrukturnya yang bersaiz butiran lebih kecil dengan kandungan Mn yang lebih tinggi.



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I certify that a Thesis Examination Committee has met on 19 October 2009 to conduct the final examination of Nor Hayati binti Alias on her thesis entitled “Dielectric and Magnetic Characterization of $(\text{La}_{0.5-x}\text{Pr}_x\text{Ba}_{0.5})(\text{Mn}_{0.5}\text{Ti}_{0.5})\text{O}_3$ Perovskite as a Multiferroic Material via Solid State Technique” in accordance with the Universities and University Colleges Act 1971 and the Constitution of the Universiti Putra Malaysia [P.U.(A) 106] 15 March 1998. The Committee recommends that the student be awarded the Master of Science.

Members of the Examination Committee are as follows:



This thesis was submitted to the Senate of Universiti Putra Malaysia and has been accepted as fulfillment of the requirement of the degree of Master of Science. The members of the Supervisory Committee were as follows:

Abdul Halim Shaari, PhD

Professor
Faculty of Science
Universiti Putra Malaysia
(Chairman)

Wan Mohamad Daud Wan Yusoff

Associate Professor
Faculty of Science
Universiti Putra Malaysia
(Member)

Che Seman Mahmood

Dr
Industrial Technology Group
Malaysian Technology Group
(Member)

HASANAH MOHD GHAZALI, PhD

Professor and Dean
School of Graduate Studies
Universiti Putra Malaysia

Date: 14 January 2010



DECLARATION

I hereby declare that the thesis is based on my original work except for quotations and citations which have been duly acknowledged. I also declare that it has not been previously or concurrently submitted for any other degree at UPM or other institutions.

NOR HAYATI BT. ALIAS

Date: 4 December 2009



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